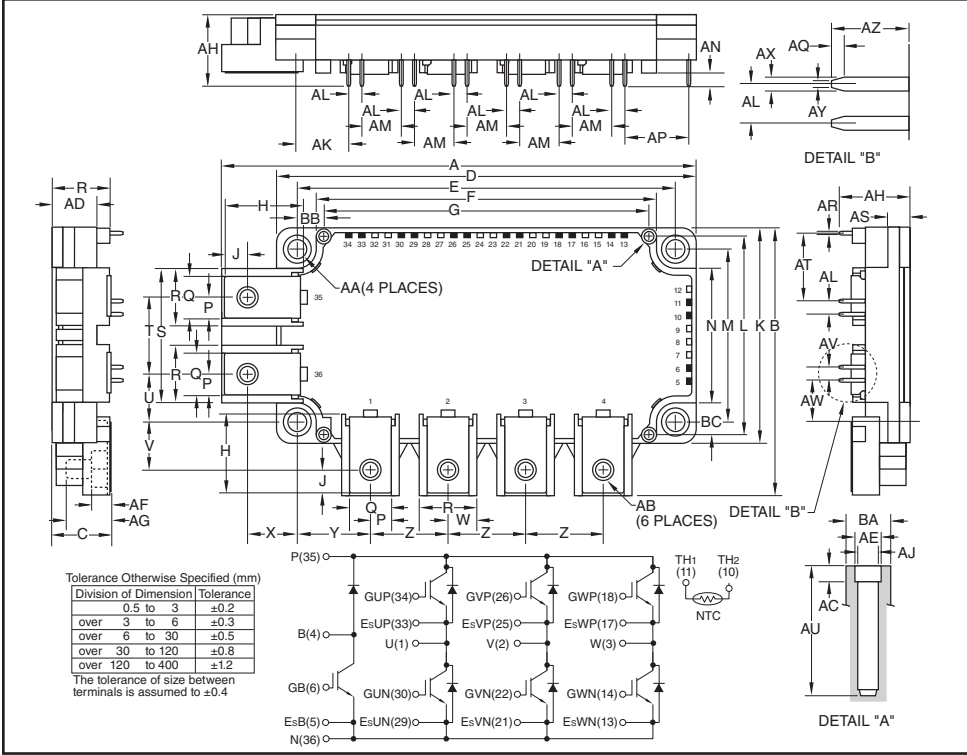


Six IGBT + Brake NX-Series Module 100 Amperes/1200 Volts



Description:

Powerex IGBT Modules are designed for use in switching applications. Each module consists of six IGBT Transistors in a three phase bridge configuration and a seventh IGBT with free-wheel diode for dynamic braking. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:

- Low Drive Power
- Low $V_{CE(sat)}$
- Discrete Super-Fast Recovery Free-Wheel Diode
- Isolated Baseplate for Easy Heat Sinking

Applications:

- AC Motor Control
- Motion/Servo Control
- Photovoltaic/Fuel Cell

Ordering Information:

Example: Select the complete module number you desire from the table below -i.e. CM100RX-24S is a 1200V (V_{CES}), 100 Ampere Six-IGBT + Brake Power Module.

Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	5.39	136.9
B	3.03	77.1
C	0.67+0.04/-0.02	17.0+1.0/-0.5
D	4.79	121.7
E	4.33±0.02	110.0±0.5
F	3.89	99.0
G	3.72	94.5
H	0.83	21.14
J	0.37	6.5
K	2.44	62.0
L	2.26	57.5
M	1.97±0.02	50.0±0.5
N	1.53	39.0
P	0.24	6.0
Q	0.48	12.0
R	0.67	17.0
S	1.53	39.0
T	0.87	22.0
U	0.55	14.0
V	0.54	13.64
W	0.33	8.5
X	0.53	13.5
Y	0.81	20.71
Z	0.9	22.86
AA	0.22 Dia.	5.5 Dia.
AB	M5	M5

Dimensions	Inches	Millimeters
AC	0.12	3.0
AD	0.51	13.0
AE	0.102 Dia.	2.6 Dia.
AF	0.21	5.4
AG	0.49	12.5
AH	0.81	20.5
AJ	0.088 Dia.	2.25 Dia.
AK	0.59	15.00
AL	0.15	3.81
AM	0.45	11.43
AN	0.14	3.5
AP	0.75	19.05
AQ	0.05	1.2
AR	0.03	0.8
AS	0.27	7.0
AT	0.77	19.68
AU	0.49	12.5
AV	0.60	15.24
AW	0.46	11.66
AX	0.04	1.15
AY	0.02	0.65
AZ	0.29	7.4
BA	0.17 Dia.	4.3 Dia.
BB	0.30	7.75
BC	0.14	3.75

Type	Current Rating Amperes	V_{CES} Volts (x 50)
CM	100	24

CM100RX-24S
Six IGBT + Brake NX-Series Module
 100 Amperes/1200 Volts

Absolute Maximum Ratings, $T_j = 25^\circ\text{C}$ unless otherwise specified

Inverter Part IGBT/FWDi

Characteristics	Symbol	Rating	Units
Collector-Emitter Voltage ($V_{GE} = 0V$)	V_{CES}	1200	Volts
Gate-Emitter Voltage ($V_{CE} = 0V$)	V_{GES}	± 20	Volts
Collector Current (DC, $T_C = 119^\circ\text{C}$) ^{*2,*4}	I_C	100	Amperes
Collector Current (Pulse, Repetitive) ^{*3}	I_{CRM}	200	Amperes
Total Power Dissipation ($T_C = 25^\circ\text{C}$) ^{*2,*4}	P_{tot}	750	Watts
Emitter Current ^{*2}	I_E^{*1}	100	Amperes
Emitter Current (Pulse, Repetitive) ^{*3}	I_{ERM}^{*1}	200	Amperes

Brake Part IGBT/ClampDi

Characteristics	Symbol	Rating	Units
Collector-Emitter Voltage ($V_{GE} = 0V$)	V_{CES}	1200	Volts
Gate-Emitter Voltage ($V_{CE} = 0V$)	V_{GES}	± 20	Volts
Collector Current (DC, $T_C = 125^\circ\text{C}$) ^{*2,*4}	I_C	50	Amperes
Collector Current (Pulse, Repetitive) ^{*3}	I_{CRM}	100	Amperes
Total Power Dissipation ($T_C = 25^\circ\text{C}$) ^{*2,*4}	P_{tot}	425	Watts
Repetitive Peak Reverse Voltage ($V_{GE} = 0V$)	V_{RRM}	1200	Volts
Forward Current ^{*2}	I_E^{*1}	50	Amperes
Forward Current (Pulse, Repetitive) ^{*3}	I_{ERM}^{*1}	100	Amperes

Module

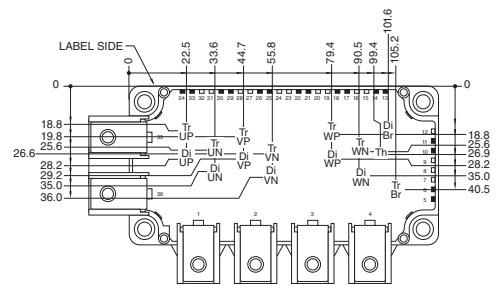
Characteristics	Symbol	Rating	Units
Isolation Voltage (Terminals to Baseplate, RMS, $f = 60\text{Hz}$, AC 1 minute)	V_{ISO}	2500	Volts
Maximum Junction Temperature, Instantaneous Event (Overload)	$T_{j(max)}$	175	$^\circ\text{C}$
Maximum Case Temperature ^{*4}	$T_C(max)$	125	$^\circ\text{C}$
Operating Junction Temperature, Continuous Operation (Under Switching)	$T_{j(op)}$	-40 to +150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 to +125	$^\circ\text{C}$

*1 Represent ratings and characteristics of the anti-parallel, emitter-to-collector free wheeling diode (FWDi).

*2 Junction temperature (T_j) should not increase beyond maximum junction temperature ($T_{j(max)}$) rating.

*3 Pulse width and repetition rate should be such that device junction temperature (T_j) does not exceed $T_{j(max)}$ rating.

*4 Case temperature (T_C) and heatsink temperature (T_s) is measured on the surface (mounting side) of the baseplate and the heatsink side just under the chips. Refer to the figure to the right for chip location. The heatsink thermal resistance should be measured just under the chips.



Each mark points to the center position of each chip.
 TrP / TrN / TrBr (* = U/V/W): IGBT DiP / DiN (* = U/V/W): FWDi
 DiBr: Clamp Th: NTC Thermistor

CM100RX-24S
Six IGBT + Brake NX-Series Module
 100 Amperes/1200 Volts

Electrical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

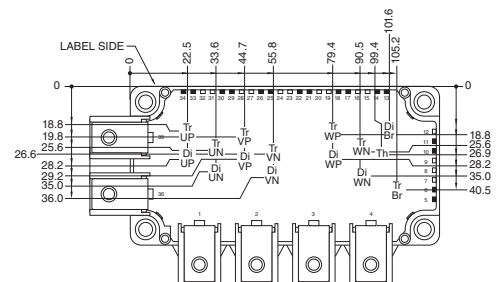
Inverter Part IGBT/FWDI

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Emitter Cutoff Current	I_{CES}	$V_{CE} = V_{CES}, V_{GE} = 0V$	—	—	1.0	mA
Gate-Emitter Leakage Current	I_{GES}	$V_{GE} = V_{GES}, V_{CE} = 0V$	—	—	0.5	μA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$I_C = 10\text{mA}, V_{CE} = 10V$	5.4	6.0	6.6	Volts
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$ (Terminal)	$I_C = 100\text{A}, V_{GE} = 15V, T_j = 25^\circ\text{C}^{*5}$	—	1.80	2.25	Volts
		$I_C = 100\text{A}, V_{GE} = 15V, T_j = 125^\circ\text{C}^{*5}$	—	2.00	—	Volts
		$I_C = 100\text{A}, V_{GE} = 15V, T_j = 150^\circ\text{C}^{*5}$	—	2.05	—	Volts
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$ (Chip)	$I_C = 100\text{A}, V_{GE} = 15V, T_j = 25^\circ\text{C}^{*5}$	—	1.70	2.15	Volts
		$I_C = 100\text{A}, V_{GE} = 15V, T_j = 125^\circ\text{C}^{*5}$	—	1.90	—	Volts
		$I_C = 100\text{A}, V_{GE} = 15V, T_j = 150^\circ\text{C}^{*5}$	—	1.95	—	Volts
Input Capacitance	C_{ies}		—	—	10	nF
Output Capacitance	C_{oes}	$V_{CE} = 10V, V_{GE} = 0V$	—	—	2.0	nF
Reverse Transfer Capacitance	C_{res}		—	—	0.17	nF
Gate Charge	Q_G	$V_{CC} = 600V, I_C = 100A, V_{GE} = 15V$	—	233	—	nC
Turn-on Delay Time	$t_{d(on)}$		—	—	300	ns
Rise Time	t_r	$V_{CC} = 600V, I_C = 100A, V_{GE} = \pm 15V,$	—	—	200	ns
Turn-off Delay Time	$t_{d(off)}$	$R_G = 6.2\Omega, \text{Inductive Load}$	—	—	600	ns
Fall Time	t_f		—	—	300	ns
Emitter-Collector Voltage	V_{EC}^{*1} (Terminal)	$I_E = 100A, V_{GE} = 0V, T_j = 25^\circ\text{C}^{*5}$	—	1.80	2.25	Volts
		$I_E = 100A, V_{GE} = 0V, T_j = 125^\circ\text{C}^{*5}$	—	1.80	—	Volts
		$I_E = 100A, V_{GE} = 0V, T_j = 150^\circ\text{C}^{*5}$	—	1.80	—	Volts
Emitter-Collector Voltage	V_{EC}^{*1} (Chip)	$I_E = 100A, V_{GE} = 0V, T_j = 25^\circ\text{C}^{*5}$	—	1.70	2.15	Volts
		$I_E = 100A, V_{GE} = 0V, T_j = 125^\circ\text{C}^{*5}$	—	1.70	—	Volts
		$I_E = 100A, V_{GE} = 0V, T_j = 150^\circ\text{C}^{*5}$	—	1.70	—	Volts
Reverse Recovery Time	t_{rr}^{*1}	$V_{CC} = 600V, I_E = 100A, V_{GE} = \pm 15V$	—	—	300	ns
Reverse Recovery Charge	Q_{rr}^{*1}	$R_G = 6.2\Omega, \text{Inductive Load}$	—	5.3	—	μC
Turn-on Switching Energy per Pulse	E_{on}	$V_{CC} = 600V, I_C = I_E = 100A,$	—	8.6	—	mJ
Turn-off Switching Energy per Pulse	E_{off}	$V_{GE} = \pm 15V, R_G = 6.2\Omega,$	—	10.7	—	mJ
Reverse Recovery Energy per Pulse	E_{rr}^{*1}	$T_j = 150^\circ\text{C}, \text{Inductive Load}$	—	10.2	—	mJ
Internal Lead Resistance	$R_{CC}^{*4} + EE^{*4}$	Main Terminals-Chip, Per Switch, $T_C = 25^\circ\text{C}^{*4}$	—	—	3.5	$\text{m}\Omega$
Internal Gate Resistance	r_g	Per Switch	—	0	—	Ω

*1 Represent ratings and characteristics of the anti-parallel, emitter-to-collector free wheeling diode (FWDI).

*4 Case temperature (T_C) and heatsink temperature (T_S) is measured on the surface (mounting side) of the baseplate and the heatsink side just under the chips. Refer to the figure to the right for chip location. The heatsink thermal resistance should be measured just under the chips.

*5 Pulse width and repetition rate should be such as to cause negligible temperature rise.



Each mark points to the center position of each chip.
 Tr*P / Tr*N / Tr*Br (* = U/V/W); IGBT Di*P / Di*N (* = U/V/W); FWDI
 DiBr: Clamp Th: NTC Thermistor

CM100RX-24S
Six IGBT + Brake NX-Series Module
 100 Amperes/1200 Volts

Electrical Characteristics, T_j = 25°C unless otherwise specified

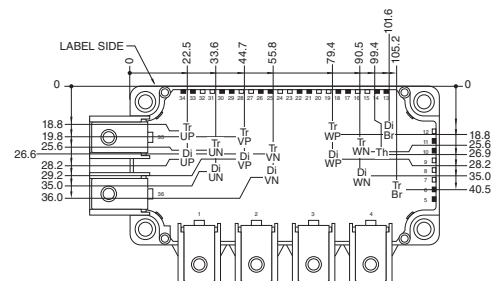
Brake Part IGBT/ClampDi

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Emitter Cutoff Current	I _{CES}	V _{CE} = V _{CES} , V _{GE} = 0V	—	—	1.0	mA
Gate-Emitter Leakage Current	I _{GES}	V _{GE} = V _{GES} , V _{CE} = 0V	—	—	0.5	μA
Gate-Emitter Threshold Voltage	V _{GE(th)}	I _C = 5mA, V _{CE} = 10V	5.4	6.0	6.6	Volts
Collector-Emitter Saturation Voltage	V _{CE(sat)} (Terminal)	I _C = 50A, V _{GE} = 15V, T _j = 25°C*5	—	1.80	2.25	Volts
		I _C = 50A, V _{GE} = 15V, T _j = 125°C*5	—	2.00	—	Volts
		I _C = 50A, V _{GE} = 15V, T _j = 150°C*5	—	2.05	—	Volts
Collector-Emitter Saturation Voltage	V _{CE(sat)} (Chip)	I _C = 50A, V _{GE} = 15V, T _j = 25°C*5	—	1.70	2.15	Volts
		I _C = 50A, V _{GE} = 15V, T _j = 125°C*5	—	1.90	—	Volts
		I _C = 50A, V _{GE} = 15V, T _j = 150°C*5	—	1.95	—	Volts
Input Capacitance	C _{ies}		—	—	5.1	nF
Output Capacitance	C _{oes}	V _{CE} = 10V, V _{GE} = 0V	—	—	0.45	nF
Reverse Transfer Capacitance	C _{res}		—	—	0.1	nF
Gate Charge	Q _G	V _{CC} = 600V, I _C = 50A, V _{GE} = 15V	—	150	—	nC
Turn-on Delay Time	t _{d(on)}		—	—	300	ns
Rise Time	t _r	V _{CC} = 600V, I _C = 50A, V _{GE} = ±15V,	—	—	200	ns
Turn-off Delay Time	t _{d(off)}	R _G = 13Ω, Inductive Load	—	—	600	ns
Fall Time	t _f		—	—	300	ns
Repetitive Peak Reverse Current	I _{RRM}	V _R = V _{RRM} , V _{GE} = 0V	—	—	1.0	mA
Forward Voltage	V _F (Terminal)	I _E = 50A, V _{GE} = 0V, T _j = 25°C*5	—	1.80	2.25	Volts
		I _E = 50A, V _{GE} = 0V, T _j = 125°C*5	—	1.80	—	Volts
		I _E = 50A, V _{GE} = 0V, T _j = 150°C*5	—	1.80	—	Volts
Forward Voltage	V _F (Chip)	I _E = 50A, V _{GE} = 0V, T _j = 25°C*5	—	1.70	2.15	Volts
		I _E = 50A, V _{GE} = 0V, T _j = 125°C*5	—	1.70	—	Volts
		I _E = 50A, V _{GE} = 0V, T _j = 150°C*5	—	1.70	—	Volts
Reverse Recovery Time	t _{rr} *1	V _{CC} = 600V, I _E = 50A, V _{GE} = ±15V	—	—	300	ns
Reverse Recovery Charge	Q _{rr} *1	R _G = 13Ω, Inductive Load	—	2.7	—	μC
Turn-on Switching Energy per Pulse	E _{on}	V _{CC} = 600V, I _C = I _E = 50A,	—	5.5	—	mJ
Turn-off Switching Energy per Pulse	E _{off}	V _{GE} = ±15V, R _G = 50Ω,	—	5.3	—	mJ
Reverse Recovery Energy per Pulse	E _{rr} *1	T _j = 150°C, Inductive Load	—	4.5	—	mJ
Internal Gate Resistance	r _g		—	0	—	Ω

*1 Represent ratings and characteristics of the anti-parallel, emitter-to-collector free wheeling diode (FWDi).

*4 Case temperature (T_C) and heatsink temperature (T_S) is measured on the surface (mounting side) of the baseplate and the heatsink side just under the chips. Refer to the figure to the right for chip location. The heatsink thermal resistance should be measured just under the chips.

*5 Pulse width and repetition rate should be such as to cause negligible temperature rise.



Each mark points to the center position of each chip.
 Tr*P / Tr*N / TrBr (* = U/W/W): IGBT Di*P / Di*N (* = U/W/W): FWDi
 DiBr: Clamp Th: NTC Thermistor

CM100RX-24S
Six IGBT + Brake NX-Series Module
 100 Amperes/1200 Volts

Electrical Characteristics, T_j = 25°C unless otherwise specified (continued)

NTC Thermistor Part

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Zero Power Resistance	R ₂₅	T _C = 25°C* ⁴	4.85	5.00	5.15	kΩ
Deviation of Resistance	ΔR/R	T _C = 100°C* ⁴ , R ₁₀₀ = 493Ω	-7.3	—	+7.8	%
B Constant	B _(25/50)	Approximate by Equation* ⁶	—	3375	—	K
Power Dissipation	P ₂₅	T _C = 25°C* ⁴	—	—	10	mW

Thermal Resistance Characteristics

Thermal Resistance, Junction to Case* ⁴	R _{th(j-c)Q}	Per Inverter IGBT	—	—	0.20	K/W
Thermal Resistance, Junction to Case* ⁴	R _{th(j-c)D}	Per Inverter FWDi	—	—	0.29	K/W
Thermal Resistance, Junction to Case* ⁴	R _{th(j-c)Q}	Per Brake IGBT	—	—	0.35	K/W
Thermal Resistance, Junction to Case* ⁴	R _{th(j-c)D}	Per Brake ClampDi	—	—	0.63	K/W
Contact Thermal Resistance, Case to Heatsink* ⁴	R _{th(c-f)}	Thermal Grease Applied, Per 1 Module* ⁷	—	15	—	K/kW

Mechanical Characteristics

Mounting Torque	M _t	Main Terminal, M5 Screw	22	27	31	in-lb
Mounting Torque	M _s	Mounting to Heatsink, M5 Screw	22	27	31	in-lb
Creepage Distance	d _s	Terminal to Terminal	10.25	—	—	mm
		Terminal to Baseplate	12.32	—	—	mm
Clearance	d _a	Terminal to Terminal	10.28	—	—	mm
		Terminal to Baseplate	10.85	—	—	mm
Weight	m			370		g
Flatness of Baseplate	e _c	On Centerline X, Y* ⁸	±0	—	±100	μm

Recommended Operating Conditions, T_a = 25°C

DC Supply Voltage	V _{CC}	Applied Across P-N Terminals	—	600	850	Volts
Gate-Emitter Drive Voltage	V _{GE(on)}	Applied Across	13.5	15.0	16.5	Volts
		G*P-Es*P/G*N-Es*N (* = U, V, W) Terminals				
External Gate Resistance	R _G	Per Switch Inverter IGBT	6.2	—	62	Ω
		Per Switch Brake IGBT	13	—	130	Ω

*⁴ Case temperature (T_C) and heatsink temperature (T_S) is measured on the surface (mounting side) of the baseplate and the heatsink side just under the chips. Refer to the figure to the right for chip location. The heatsink thermal resistance should be measured just under the chips.

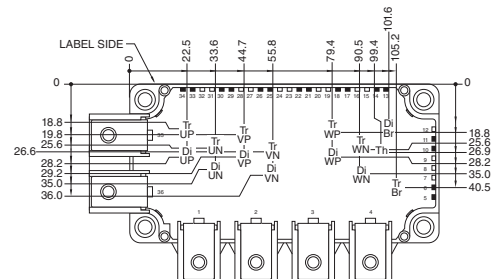
*⁶ $B_{(25/50)} = \ln\left(\frac{R_{25}}{R_{50}} \cdot \frac{1}{\frac{1}{T_{25}} - \frac{1}{T_{50}}}\right)$

R₂₅; Resistance at Absolute Temperature T₂₅ [K]; T₂₅ = 25 [°C] + 273.15 = 298.15 [K]

R₅₀; Resistance at Absolute Temperature T₅₀ [K]; T₅₀ = 50 [°C] + 273.15 = 323.15 [K]

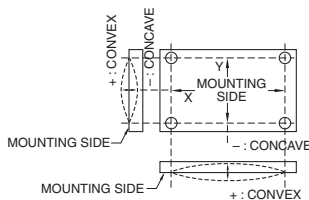
*⁷ Typical value is measured by using thermally conductive grease of λ = 0.9 [W/(m • K)].

*⁸ Baseplate (mounting side) flatness measurement points (X, Y) are shown in the figure below.



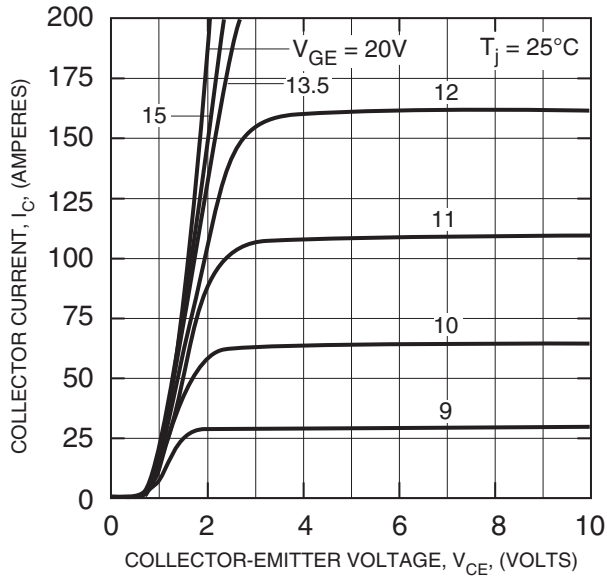
Each mark points to the center position of each chip.

Tr*P / Tr*N / TrBr (* = U/V/W); IGBT DI*P / DI*N (* = U/V/W); FWDi
 DIBr: Clamp Th: NTC Thermistor

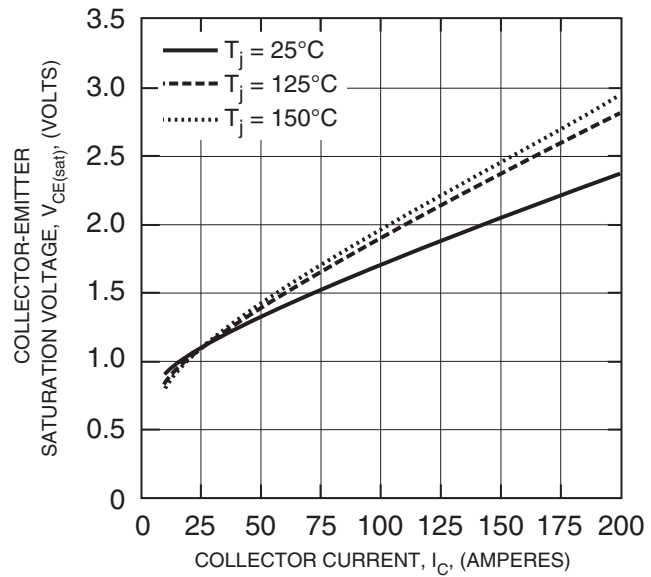


CM100RX-24S
Six IGBT + Brake NX-Series Module
 100 Amperes/1200 Volts

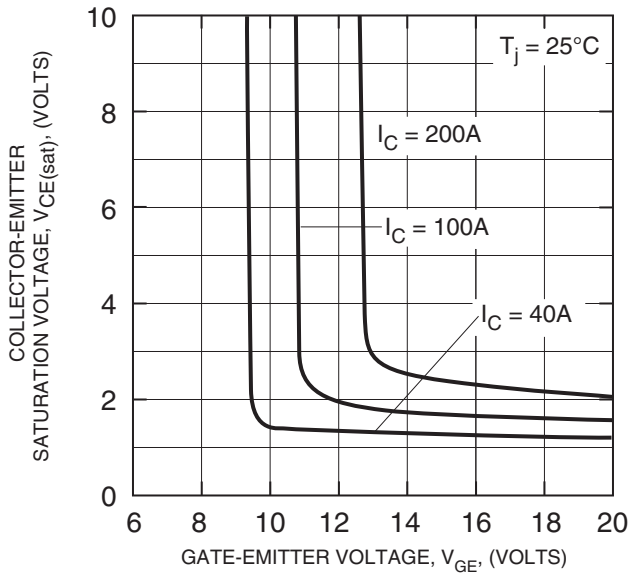
**OUTPUT CHARACTERISTICS
 (INVERTER PART - TYPICAL)**



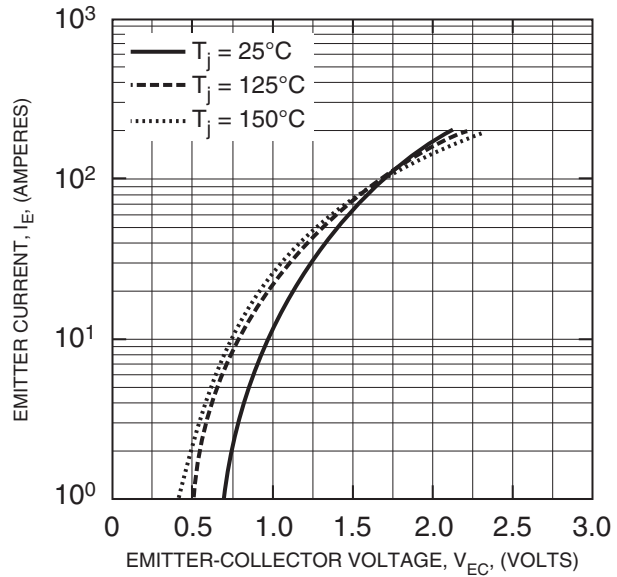
**COLLECTOR-EMITTER
 SATURATION VOLTAGE CHARACTERISTICS
 (INVERTER PART - TYPICAL)**



**COLLECTOR-EMITTER
 SATURATION VOLTAGE CHARACTERISTICS
 (INVERTER PART - TYPICAL)**

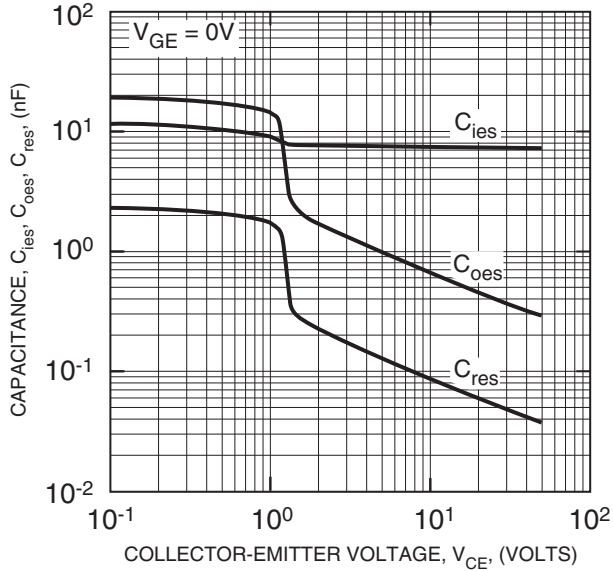


**FREE-WHEEL DIODE
 FORWARD CHARACTERISTICS
 (INVERTER PART - TYPICAL)**

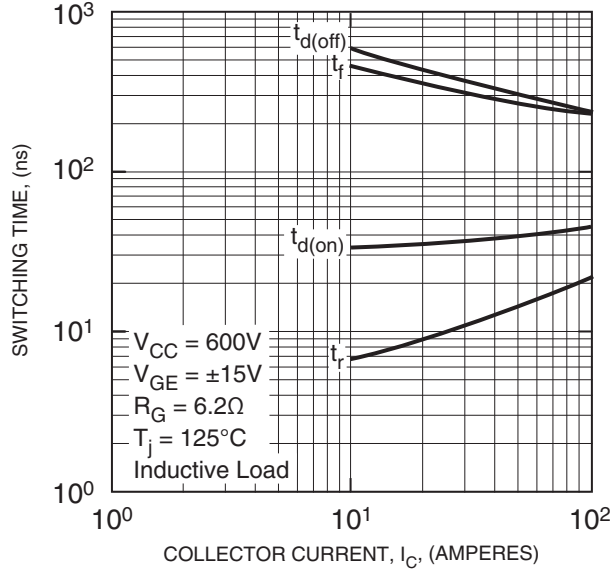


CM100RX-24S
Six IGBT + Brake NX-Series Module
 100 Amperes/1200 Volts

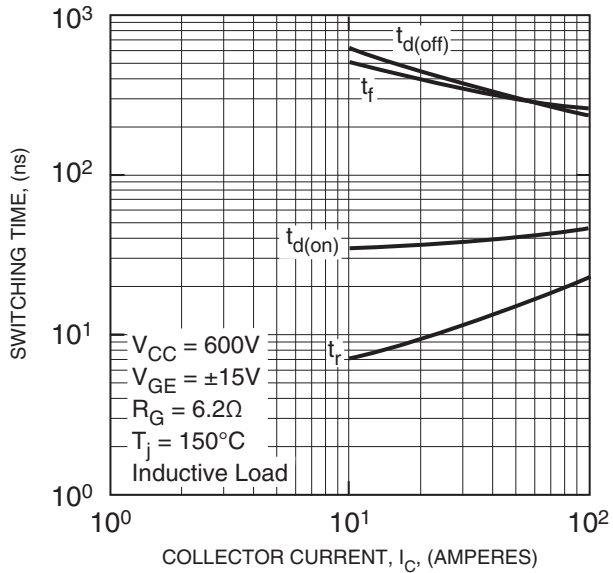
CAPACITANCE VS. V_{CE}
 (INVERTER PART - TYPICAL)



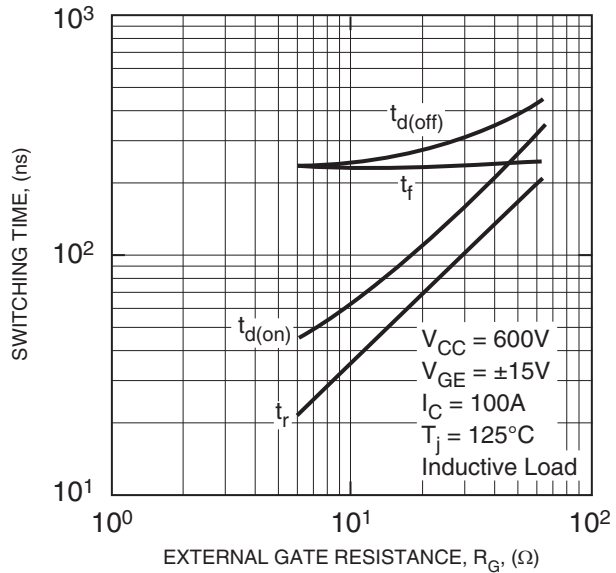
HALF-BRIDGE SWITCHING CHARACTERISTICS
 (INVERTER PART - TYPICAL)



HALF-BRIDGE SWITCHING CHARACTERISTICS
 (INVERTER PART - TYPICAL)

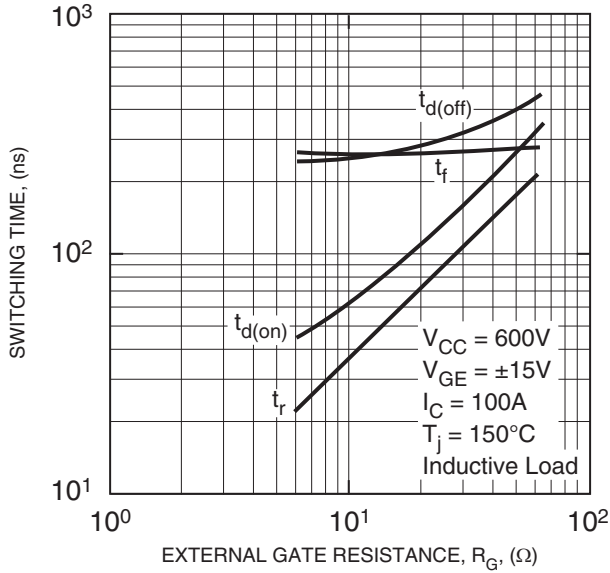


SWITCHING TIME VS. GATE RESISTANCE
 (INVERTER PART - TYPICAL)

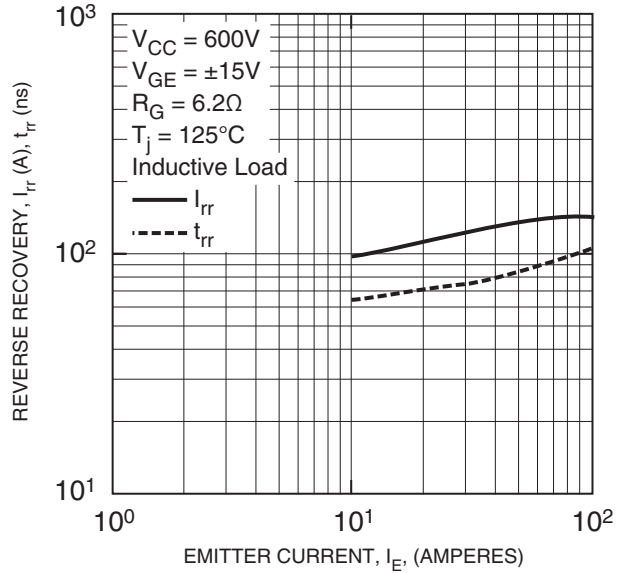


CM100RX-24S
Six IGBT + Brake NX-Series Module
 100 Amperes/1200 Volts

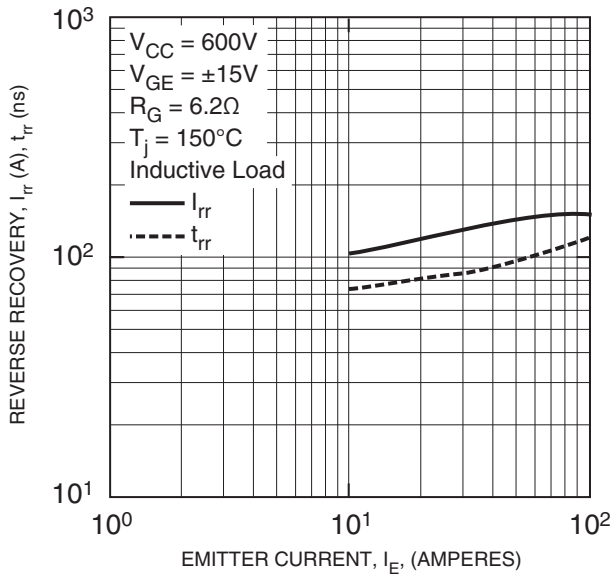
SWITCHING TIME VS. GATE RESISTANCE (INVERTER PART - TYPICAL)



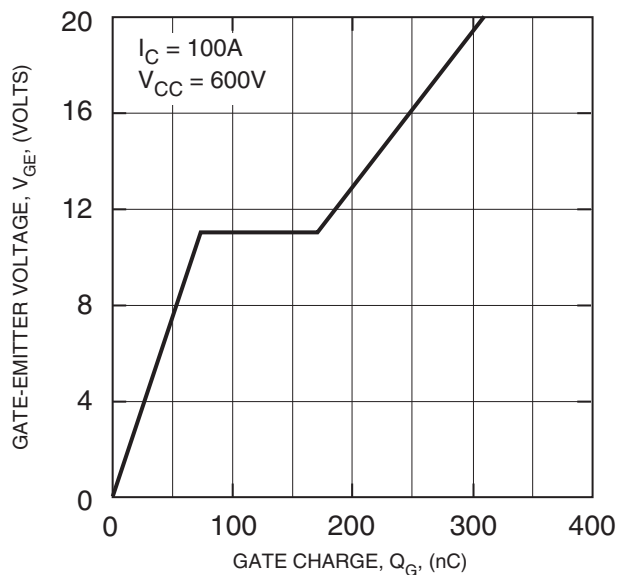
REVERSE RECOVERY CHARACTERISTICS (INVERTER PART - TYPICAL)



REVERSE RECOVERY CHARACTERISTICS (INVERTER PART - TYPICAL)

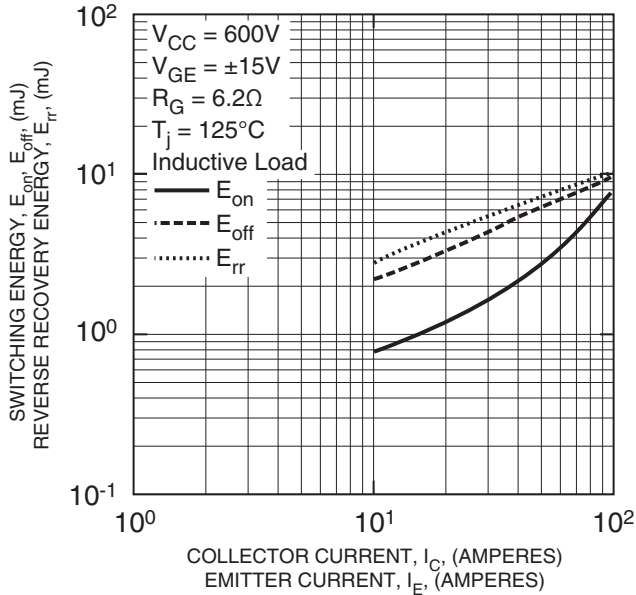


GATE CHARGE VS. V_GE (INVERTER PART)

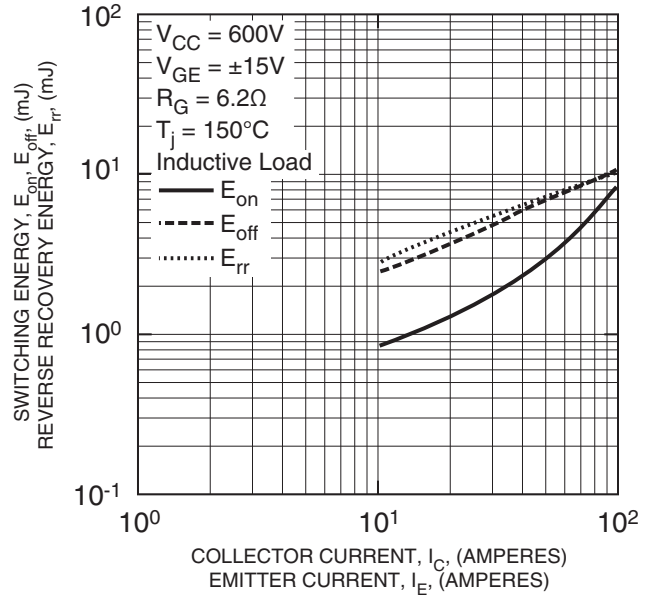


CM100RX-24S
Six IGBT + Brake NX-Series Module
 100 Amperes/1200 Volts

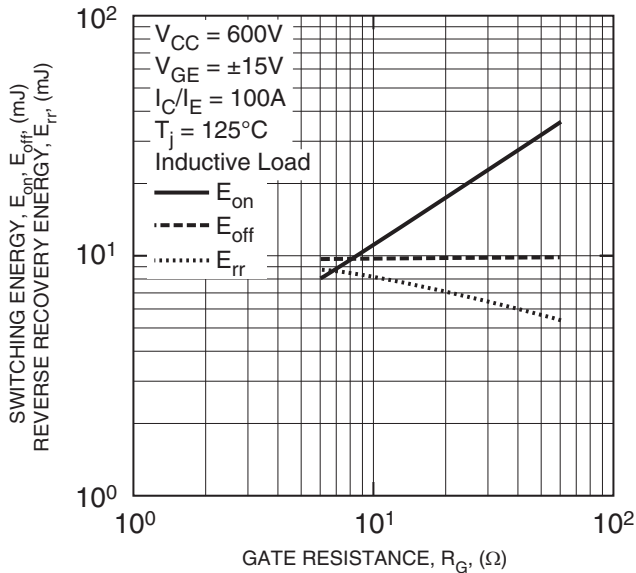
HALF-BRIDGE SWITCHING CHARACTERISTICS (INVERTER PART - TYPICAL)



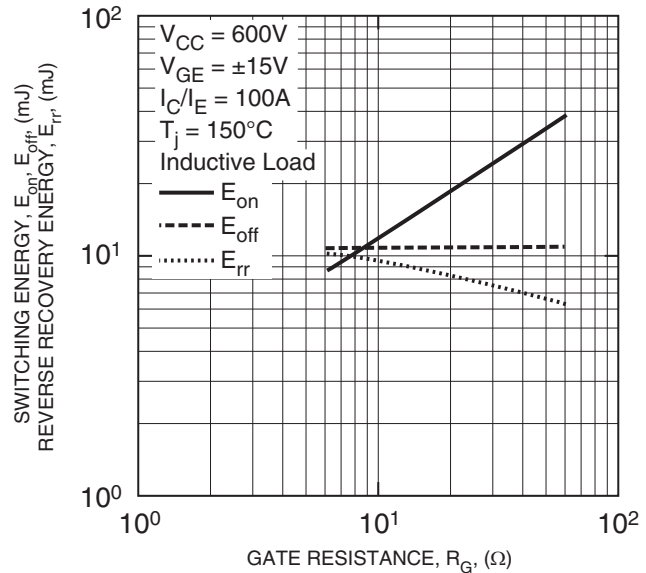
HALF-BRIDGE SWITCHING CHARACTERISTICS (INVERTER PART - TYPICAL)



HALF-BRIDGE SWITCHING CHARACTERISTICS (INVERTER PART - TYPICAL)

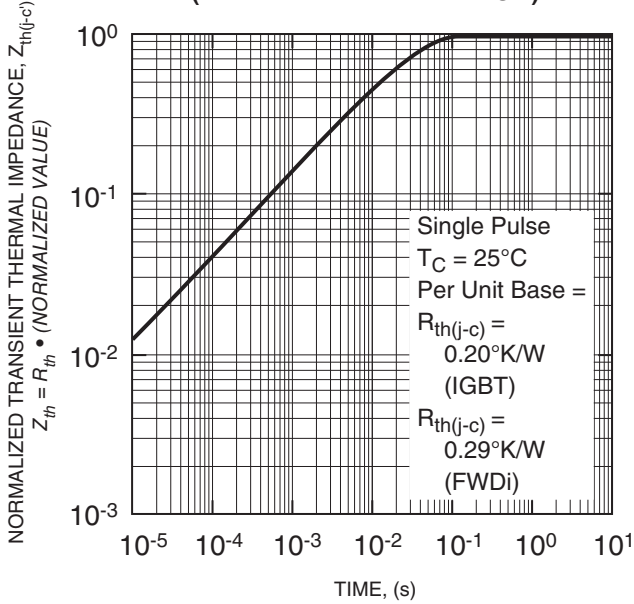


HALF-BRIDGE SWITCHING CHARACTERISTICS (INVERTER PART - TYPICAL)

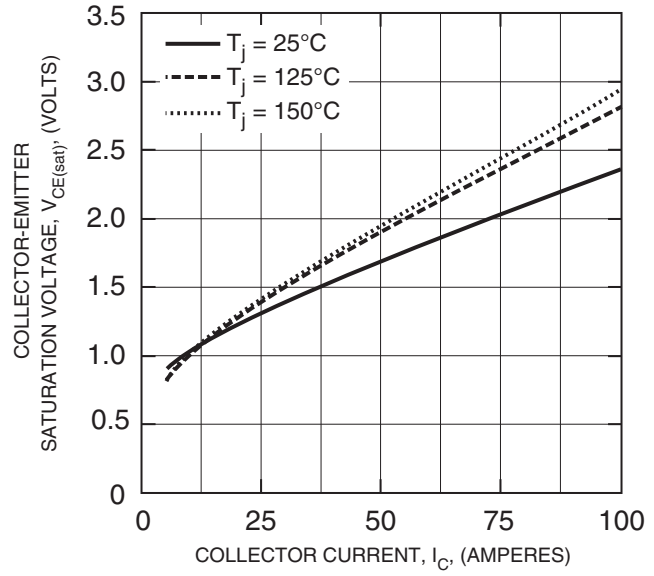


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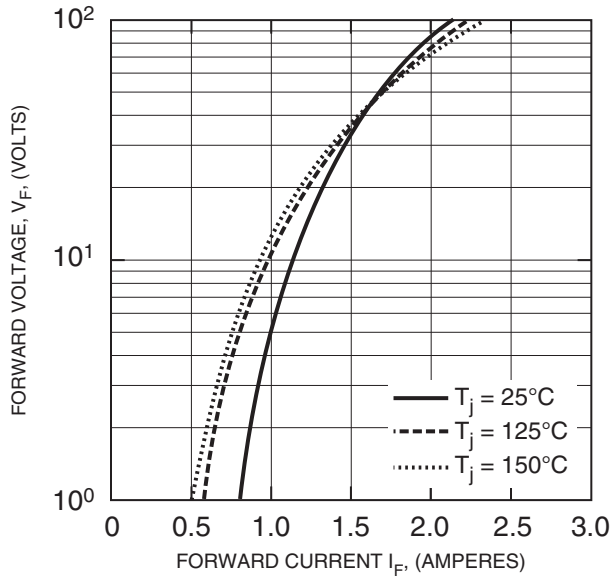
TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (INVERTER PART - MAXIMUM)



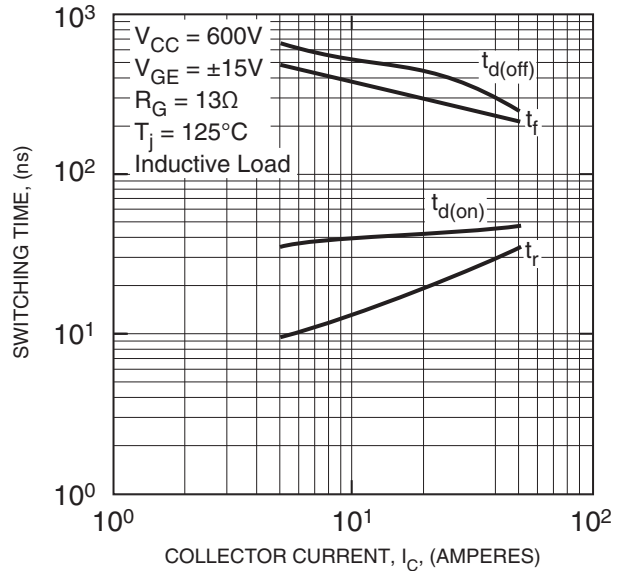
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (BRAKE PART - TYPICAL)



FREE-WHEEL DIODE FORWARD CHARACTERISTICS (BRAKE PART - TYPICAL)

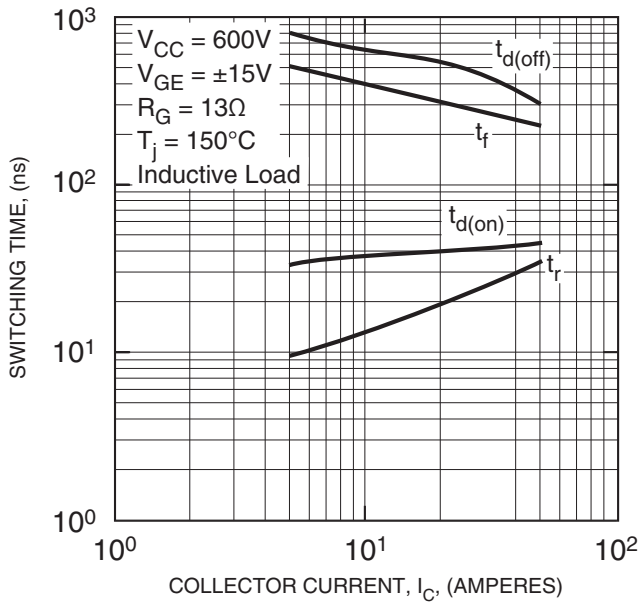


HALF-BRIDGE SWITCHING CHARACTERISTICS (BRAKE PART - TYPICAL)

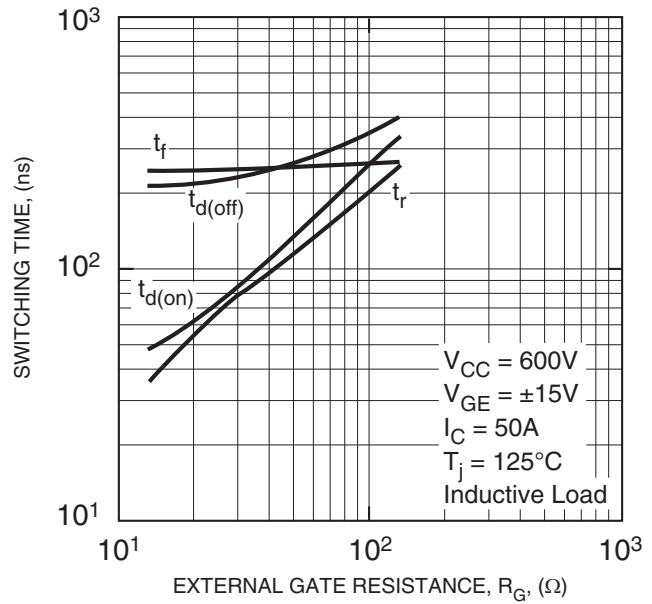


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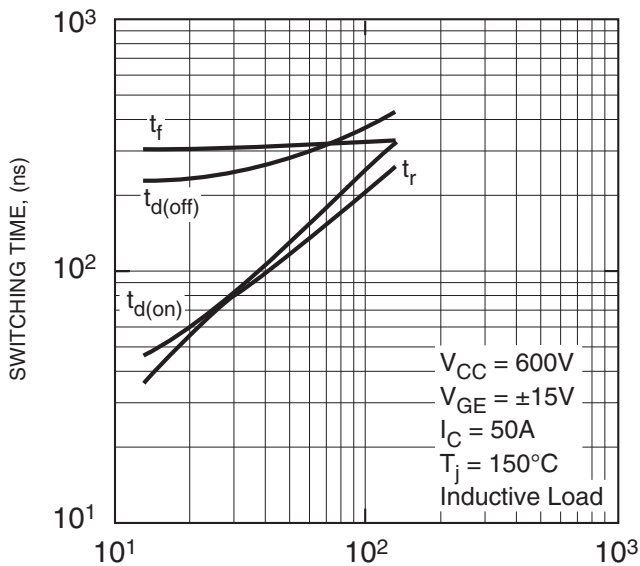
HALF-BRIDGE SWITCHING CHARACTERISTICS (BRAKE PART - TYPICAL)



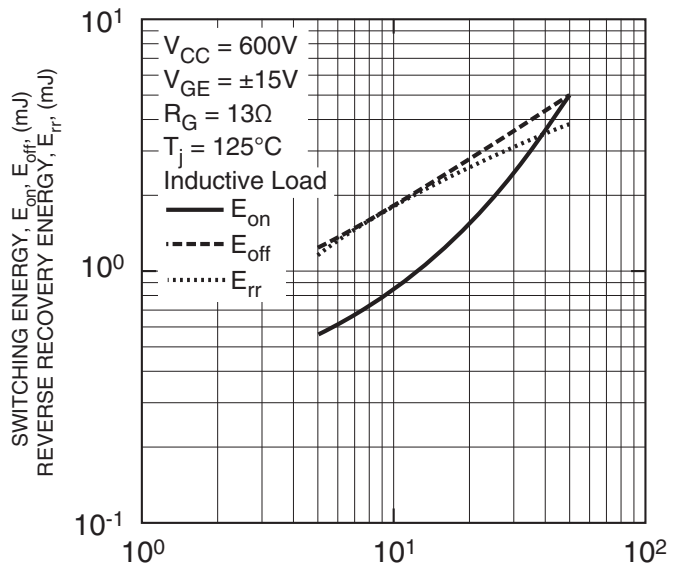
SWITCHING TIME VS. GATE RESISTANCE (BRAKE - TYPICAL)



SWITCHING TIME VS. GATE RESISTANCE (BRAKE - TYPICAL)

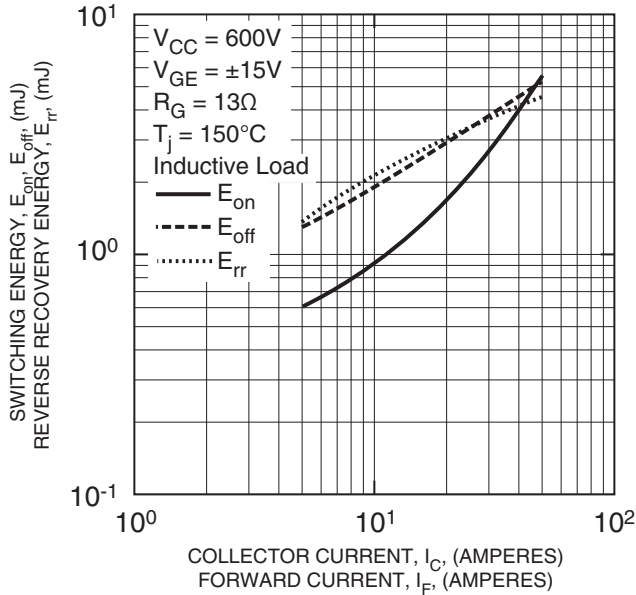


HALF-BRIDGE SWITCHING CHARACTERISTICS (BRAKE PART - TYPICAL)

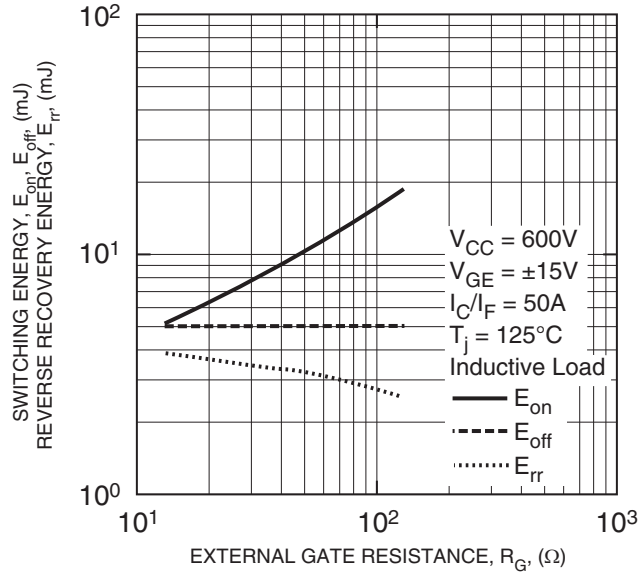


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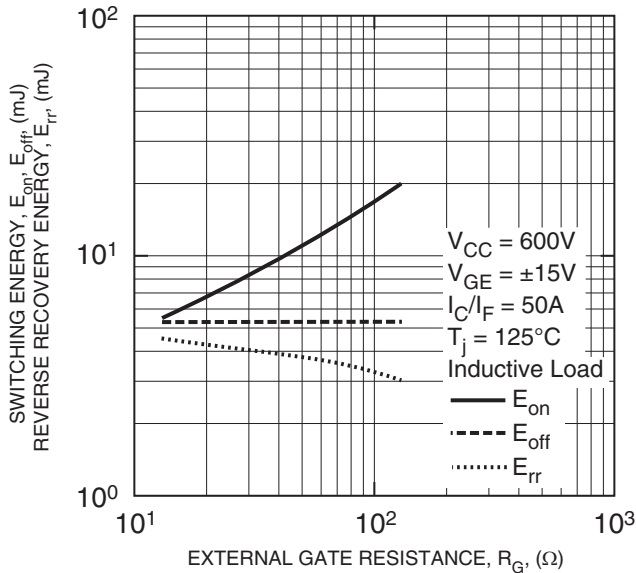
HALF-BRIDGE SWITCHING CHARACTERISTICS (BRAKE PART - TYPICAL)



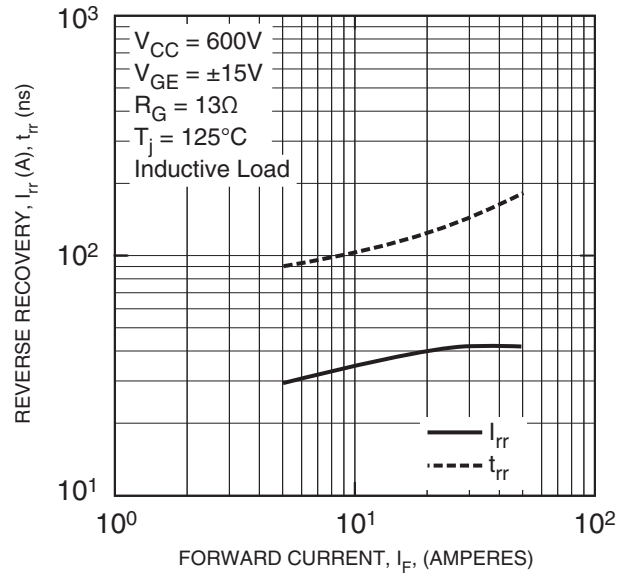
HALF-BRIDGE SWITCHING CHARACTERISTICS (BRAKE PART - TYPICAL)



HALF-BRIDGE SWITCHING CHARACTERISTICS (BRAKE PART - TYPICAL)

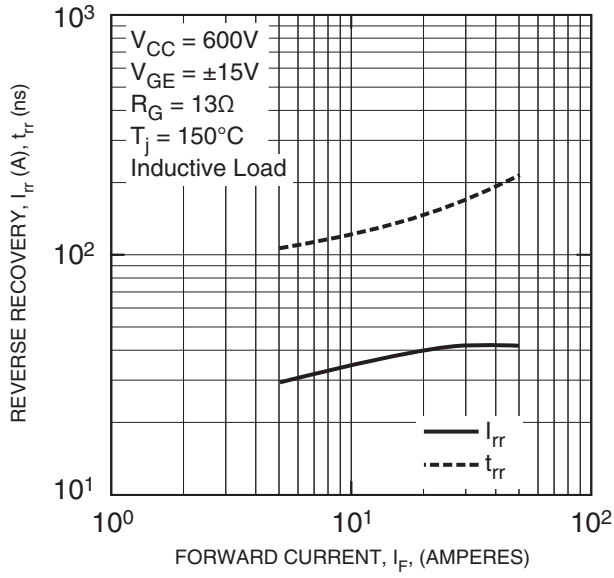


REVERSE RECOVERY CHARACTERISTICS (BRAKE PART - TYPICAL)



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**REVERSE RECOVERY CHARACTERISTICS
 (BRAKE PART - TYPICAL)**



**TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS
 (BRAKE PART - MAXIMUM)**

